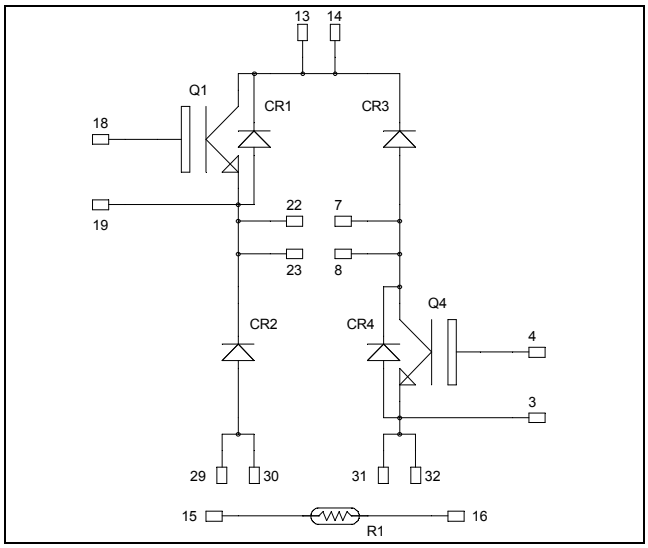
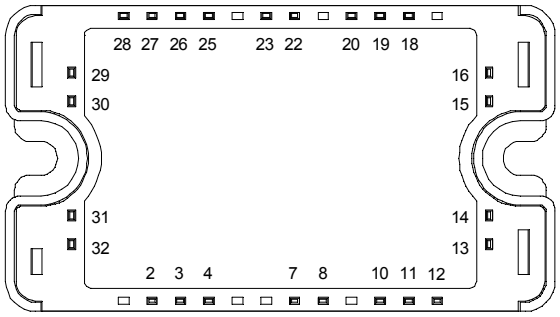
APTGT100DH60T3G

Asymmetrical - Bridge Trench + Field Stop IGBT3 Power Module

V_{CES} = 600V
I_C = 100A* @ Tc = 80°C





All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 …

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	150 *	A
		T_C = 80°C	100 *	
I_{CM}	Pulsed Collector Current	T_C = 25°C	200	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	340	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 150°C	200A @ 550V	

* Specification of IGBT device but output current must be limited to 75A to not exceed a delta of temperature greater than 30°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 600V				250	µA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} =15V I_C = 100A	T_j = 25°C		1.5	1.9	V
			T_j = 150°C		1.7		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 1.5 mA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			6100		pF
C_{oes}	Output Capacitance				390		
C_{res}	Reverse Transfer Capacitance				190		
Q_G	Gate charge	V_{GE}=±15V, I_C=100A V_{CE}=300V			1.1		µC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 100A R_G = 3.3Ω			115		ns
T_r	Rise Time				45		
$T_{d(off)}$	Turn-off Delay Time				225		
T_f	Fall Time				55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 100A R_G = 3.3Ω			130		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				300		
T_f	Fall Time				70		
E_{on}	Turn on Energy	V_{GE} = ±15V V_{Bus} = 300V I_C = 100A R_G = 3.3Ω	T_j = 25°C		0.4		mJ
			T_j = 150°C		0.875		
E_{off}	Turn off Energy		T_j = 25°C		2.5		mJ
			T_j = 150°C		3.5		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 360V t_p ≤ 6µs ; T_j = 150°C			500		A

Diode ratings and characteristics (CR2 & CR3)

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V_R=600V	T_j = 25°C			250	µA
			T_j = 150°C			500	
I_F	DC Forward Current		Tc = 80°C		100		A
V_F	Diode Forward Voltage	I_F = 100A V_{GE} = 0V	T_j = 25°C		1.6	2	V
			T_j = 150°C		1.5		
t_{rr}	Reverse Recovery Time	I_F = 100A V_R = 300V di/dt =2000A/µs	T_j = 25°C		125		ns
			T_j = 150°C		220		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		4.7		µC
			T_j = 150°C		9.9		
E_r	Reverse Recovery Energy		T_j = 25°C		1.1		mJ
			T_j = 150°C		2.4		

CR1 & CR4 are IGBT protection diodes only

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.44	°C/W
			Diode			0.77	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		175	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

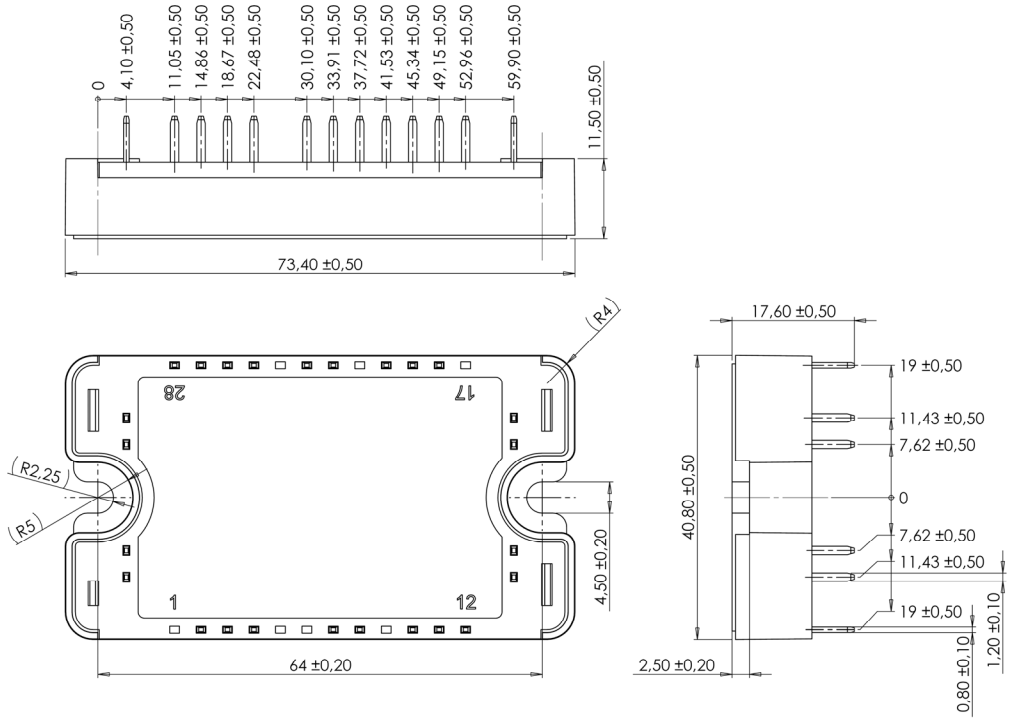
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
$\Delta B/B$		T_C=100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

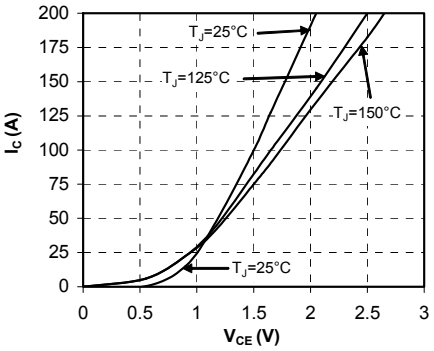
SP3 Package outline (dimensions in mm)



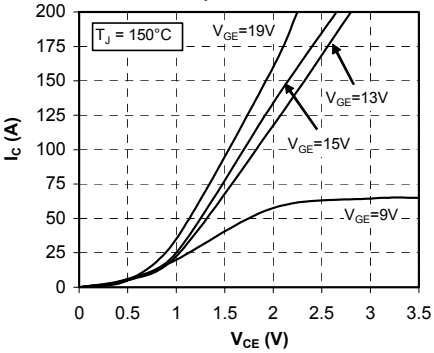
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve

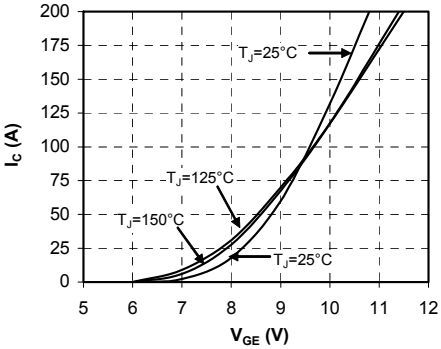
Output Characteristics (V_{GE}=15V)



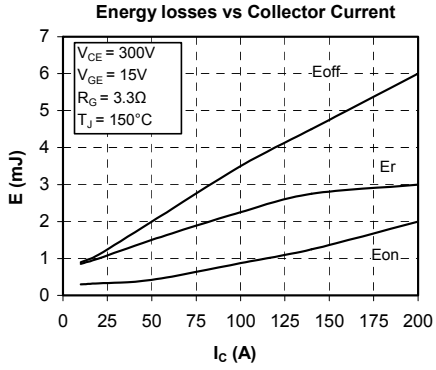
Output Characteristics



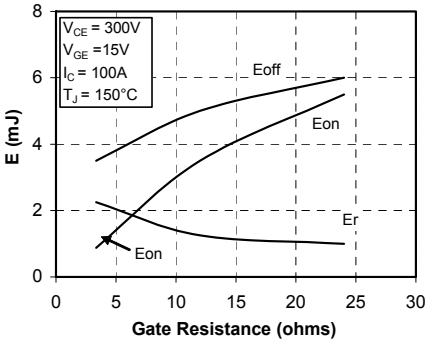
Transfert Characteristics



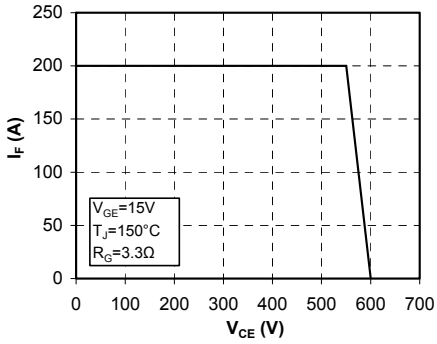
Energy losses vs Collector Current



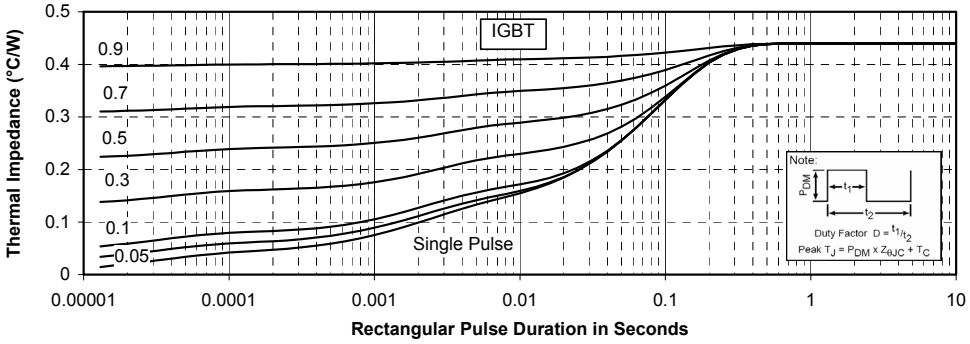
Switching Energy Losses vs Gate Resistance

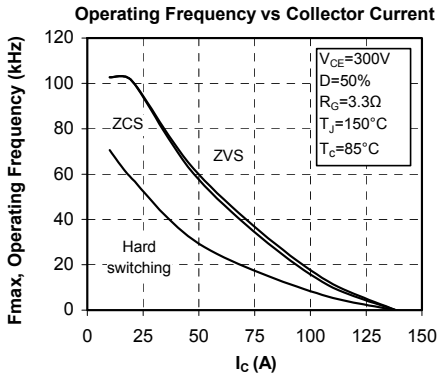


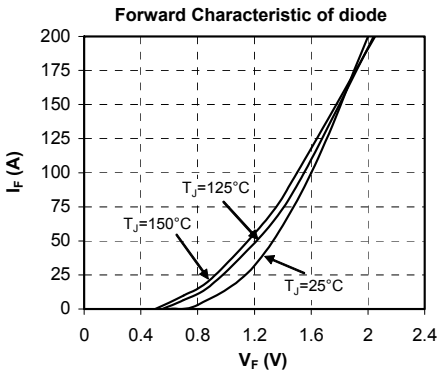
Reverse Bias Safe Operating Area

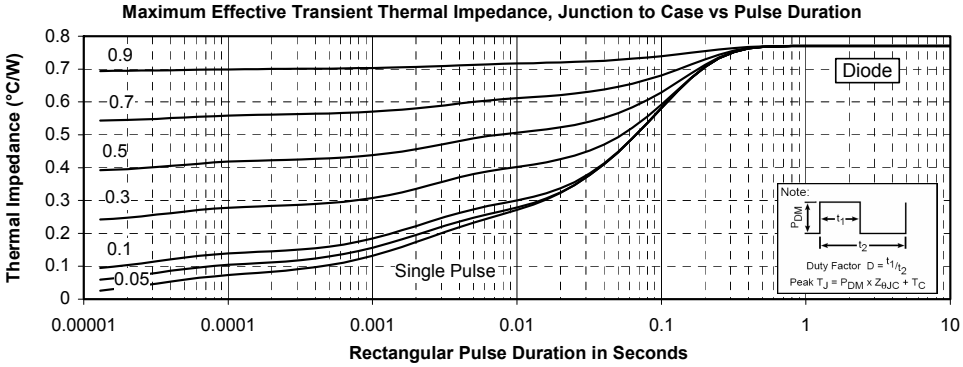


Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration




Operating Frequency vs Collector Current
Fmax, Operating Frequency (kHz)
I_C (A)
V_{CE}=300V
D=50%
R_G=3.3Ω
T_J=150°C
T_c=85°C
ZCS
ZVS
Hard switching
0
20
40
60
80
100
120
0
25
50
75
100
125
150


Forward Characteristic of diode
I_F (A)
V_F (V)
T_J=125°C
T_J=150°C
T_J=25°C
0
25
50
75
100
125
150
175
200
0
0.4
0.8
1.2
1.6
2
2.4


Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration
Thermal Impedance (°C/W)
Rectangular Pulse Duration in Seconds
0.9
0.7
0.5
0.3
0.1
0.05
Single Pulse
Diode
Note:
P_{DM}
t_1
t_2
Duty Factor $D = t_1/t_2$
Peak $T_J = P_{DM} \times Z_{\theta JC} + T_C$
0
0.1
0.2
0.3
0.4
0.5
0.6
0.7
0.8
0.00001
0.0001
0.001
0.01
0.1
1
10

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